

# NVMTSC1D3N08M7

## MOSFET - Power, Single N-Channel

### 80 V, 1.25 mΩ, 348 A

#### Features

- Small Footprint (8x8 mm) for Compact Design
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low  $Q_G$  and Capacitance to Minimize Driver Losses
- New Power 88 Dual Cool Package
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant
- Wettable Flank Plated Option For Enhanced Optical Inspection

#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	$V_{DS}$	80	V	
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V	
Continuous Drain Current $R_{\theta JCB}$ (Notes 1, 3)	Steady State	$T_C = 25^\circ\text{C}$	$I_D$ 348	A
		$T_C = 100^\circ\text{C}$	246	
Power Dissipation $R_{\theta JCB}$ (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	$P_D$ 287	W
		$T_C = 100^\circ\text{C}$	144	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$ 46	A
		$T_A = 100^\circ\text{C}$	33	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	$P_D$ 5.1	W
		$T_A = 100^\circ\text{C}$	2.6	
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	$I_{DM}$ 900	A	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode)	$I_S$	239	A	
Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 28.2 \text{ A}$ )	$E_{AS}$	2228	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case Bottom - Steady State	$R_{\theta JCB}$	0.5	$^\circ\text{C}/\text{W}$
Junction-to-Case Top - Steady State	$R_{\theta JCT}$	0.81	$^\circ\text{C}/\text{W}$
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	29	$^\circ\text{C}/\text{W}$

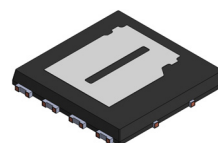
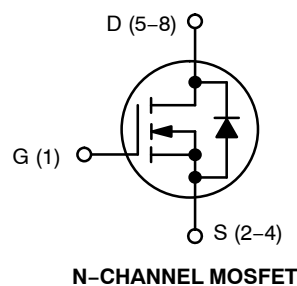
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



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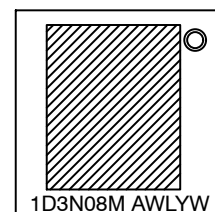
[www.onsemi.com](http://www.onsemi.com)

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
80 V	1.25 mΩ @ 10 V	348 A



DFNW8  
CASE 507AR

#### MARKING DIAGRAM



1D3N08M = Specific Device Code  
 A = Assembly Location  
 WL = Wafer Lot Code  
 Y = Year Code  
 W = Work Week Code

#### ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

# NVMTSC1D3N08M7

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	80			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			31.4		mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}$	$T_J = 25^\circ\text{C}$		1	$\mu\text{A}$
			$T_J = 125^\circ\text{C}$		250	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

## ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 330\ \mu\text{A}$	2.0		4.0	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-10		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 80\text{ A}$		0.97	1.25	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 15\text{ V}, I_D = 80\text{ A}$		253		S

## CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 40\text{ V}$		14530		$\text{pF}$
Output Capacitance	$C_{OSS}$			2047		
Reverse Transfer Capacitance	$C_{RSS}$			106		
Total Gate Charge	$Q_G(TOT)$	$V_{GS} = 10\text{ V}, V_{DS} = 40\text{ V}; I_D = 80\text{ A}$		196		$\text{nC}$
Threshold Gate Charge	$Q_G(TH)$	$V_{GS} = 10\text{ V}, V_{DS} = 40\text{ V}; I_D = 80\text{ A}$		37.3		
Gate-to-Source Charge	$Q_{GS}$			68.3		
Gate-to-Drain Charge	$Q_{GD}$			36.4		
Plateau Voltage	$V_{GP}$			4.82		V

## SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 40\text{ V}, I_D = 80\text{ A}, R_G = 2.5\ \Omega$		39.9		$\text{ns}$
Rise Time	$t_r$			29.0		
Turn-Off Delay Time	$t_{d(OFF)}$			80.9		
Fall Time	$t_f$			32.8		

## DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_S = 80\text{ A}$	$T_J = 25^\circ\text{C}$		0.80	1.2	V
			$T_J = 125^\circ\text{C}$		0.68		
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 80\text{ A}$		80.3		$\text{ns}$	
Charge Time	$t_a$			50			
Discharge Time	$t_b$			30			
Reverse Recovery Charge	$Q_{RR}$			152			nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

5. Switching characteristics are independent of operating junction temperatures.

# NVMTSC1D3N08M7

## TYPICAL CHARACTERISTICS

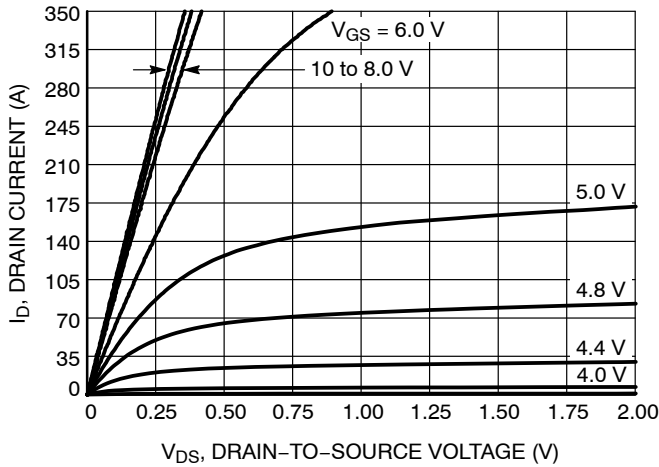


Figure 1. On-Region Characteristics

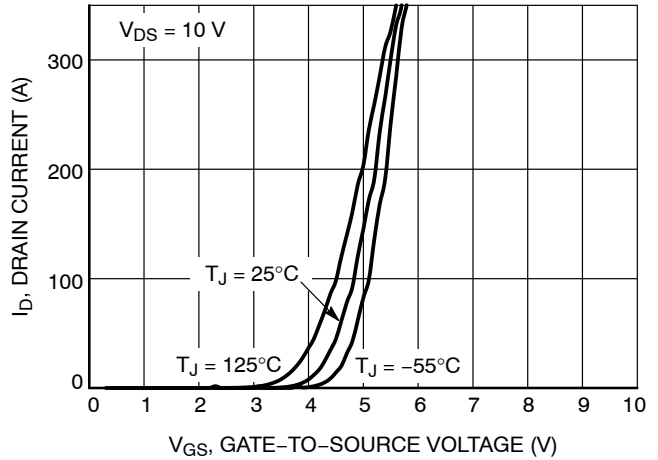


Figure 2. Transfer Characteristics

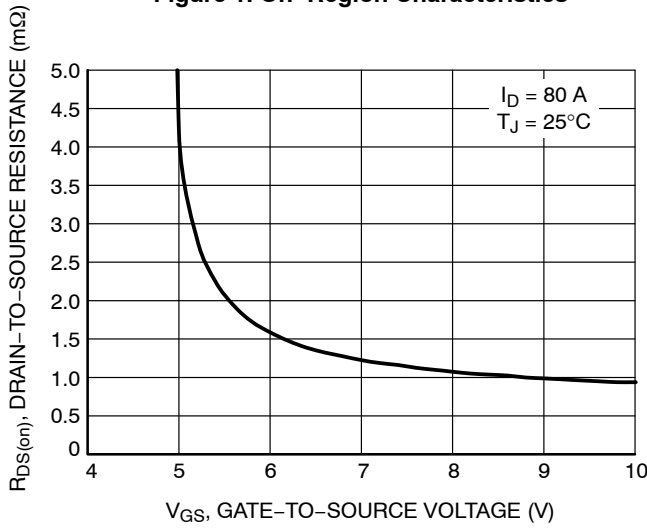


Figure 3. On-Resistance vs. Gate-to-Source Voltage

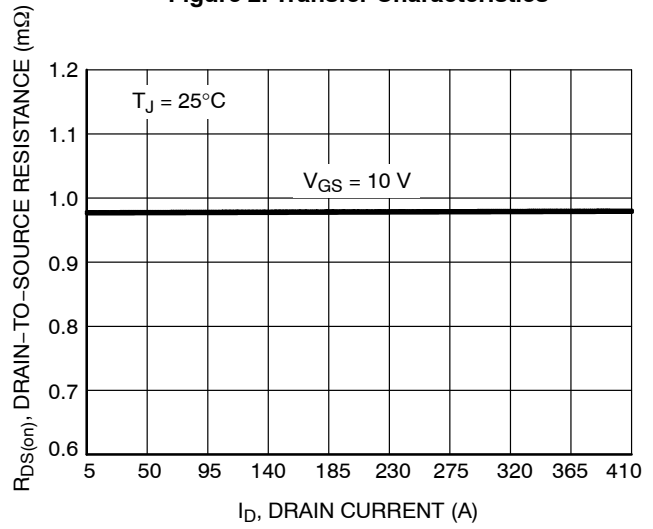


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

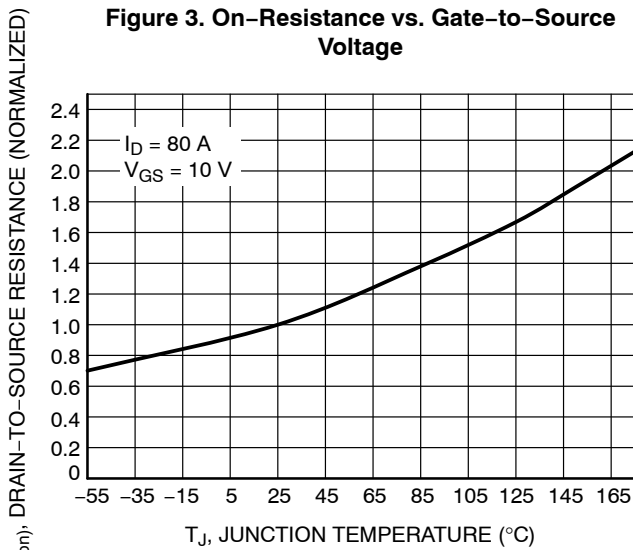


Figure 5. On-Resistance Variation with Temperature

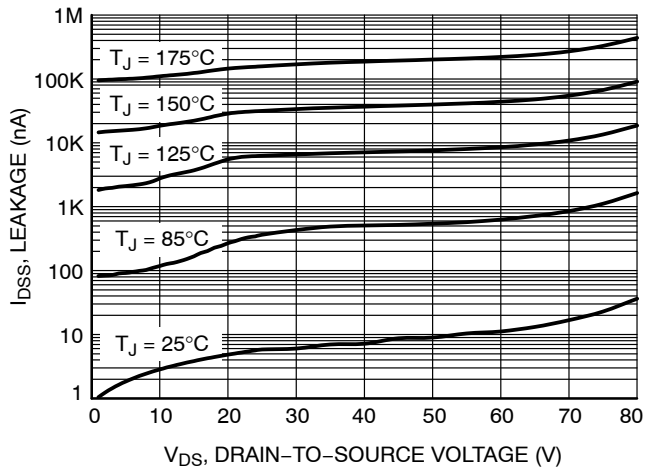
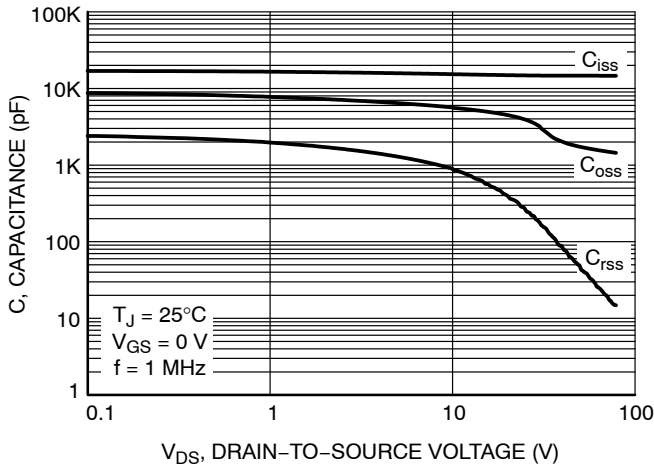


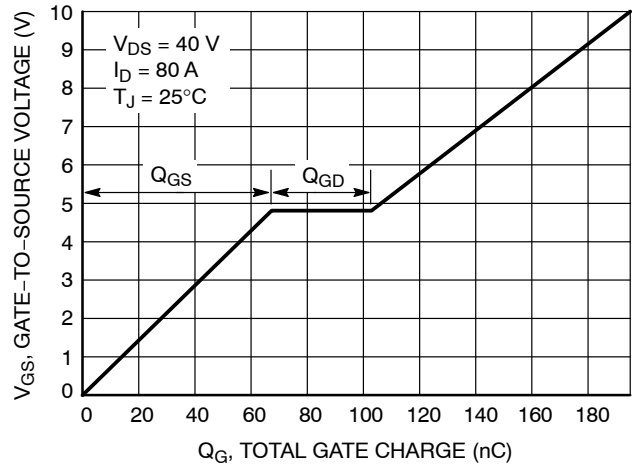
Figure 6. Drain-to-Source Leakage Current vs. Voltage

# NVMTSC1D3N08M7

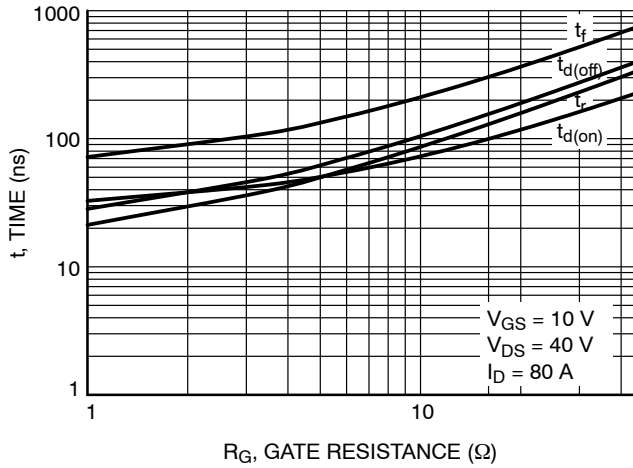
## TYPICAL CHARACTERISTICS



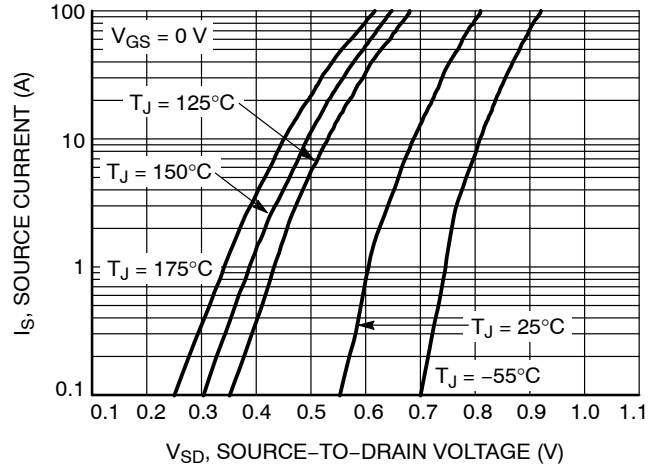
**Figure 7. Capacitance Variation**



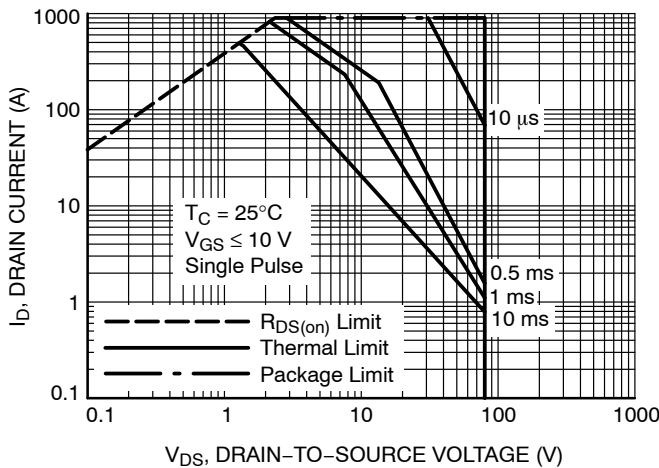
**Figure 8. Gate-to-Source vs. Total Charge**



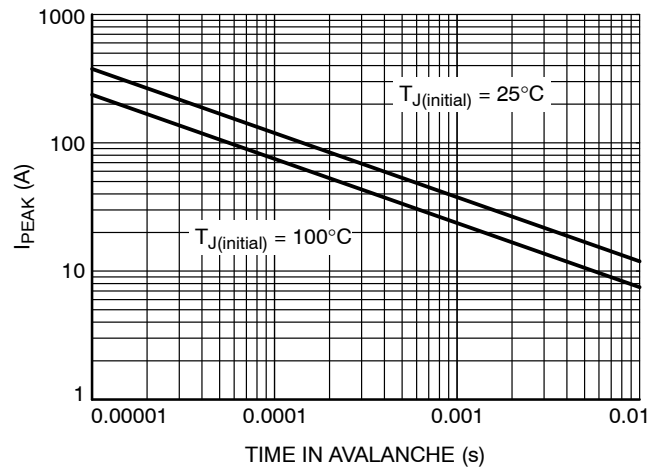
**Figure 9. Resistive Switching Time Variation vs. Gate Resistance**



**Figure 10. Diode Forward Voltage vs. Current**



**Figure 11. Maximum Rated Forward Biased Safe Operating Area**



**Figure 12. Maximum Drain Current vs. Time in Avalanche**

# NVMTSC1D3N08M7

## TYPICAL CHARACTERISTICS

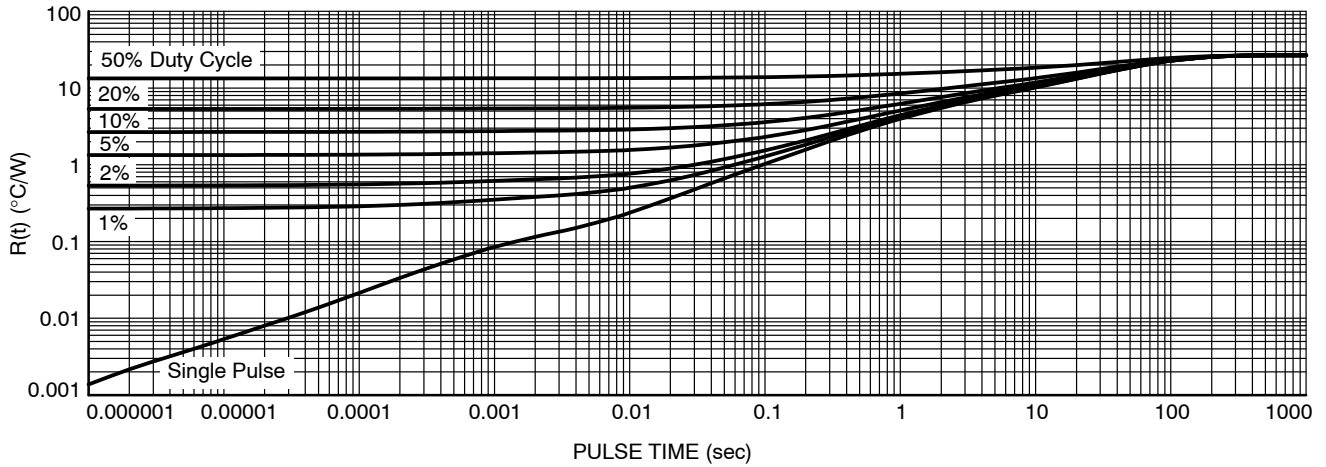


Figure 13. Thermal Response

### DEVICE ORDERING INFORMATION

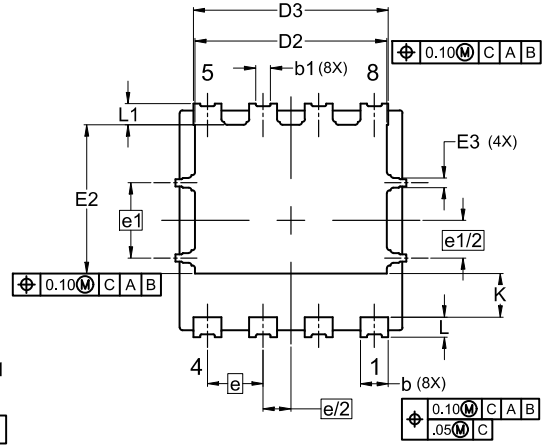
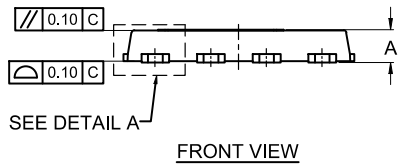
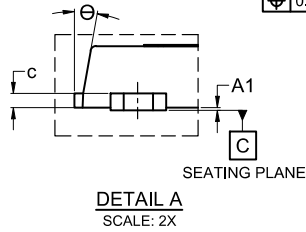
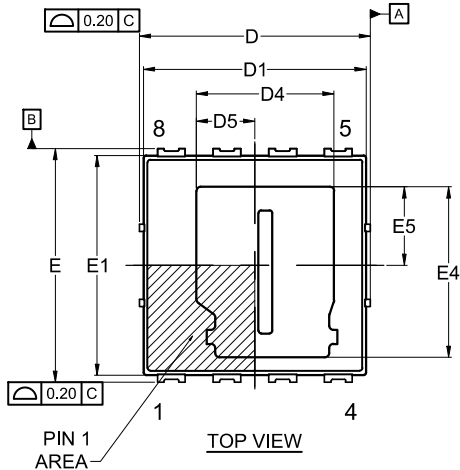
Device	Marking	Package	Shipping <sup>†</sup>
NVMTSC1D3N08M7TXG	1D3N08M	POWER 88 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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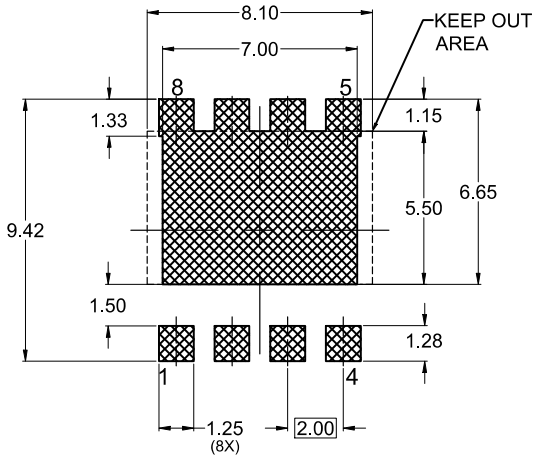
## PACKAGE DIMENSIONS

DFNW8 8.3x8.4, 2P  
CASE 507AR  
ISSUE O




### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.85	0.95	1.05
A1	0.00	—	0.05
b	0.90	1.00	1.10
b1	0.43	0.53	0.63
c	0.23	0.28	0.33
D	8.20	8.30	8.40
D1	7.90	8.00	8.10
D2	6.80	6.90	7.00
D3	6.90	7.00	7.10
D4	4.85	4.95	5.05
D5	2.00	2.10	2.20
E	8.30	8.40	8.50
E1	7.80	7.90	8.00
E2	5.24	5.34	5.44
E3	0.25	0.35	0.45
E4	6.03	6.13	6.23
E5	2.72	2.82	2.92
e	2.00 BSC		
e/2	1.00 BSC		
e1	2.70 BSC		
e1/2	1.35 BSC		
K	1.50	1.57	1.70
L	0.64	0.74	0.84
L1	0.67	0.77	0.87
θ	0°	—	12°

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